

1. Scope

The present specifications shall apply to an FMEN-215A.

2. Outline

Type	Silicon Schottky Barrier Diode
Structure	Resin Molded
Applications	High Frequency Rectification

3. Flammability

UL94V-0(Equivalent)

4. Absolute maximum ratings

No.	Item	Symbol	Unit	Rating	Conditions
1	Transient Peak Reverse Voltage	V_{RSM}	V	100	
2	Peak Reverse Voltage	V_{RM}	V	100	
3	Average Forward Current	$I_{F(AV)}$	A	15	Refer to Derating of 7
4	Peak Surge Forward Current	I_{FSM}	A	100	10msec. Half sinewave, one shot
5	I^2t Limiting Value	I^2t	A^2s	50	$1msec \leq t \leq 10msec$
6	Junction Temperature	T_j	$^{\circ}C$	-40~+150	
7	Storage Temperature	T_{stg}	$^{\circ}C$	-40~+150	

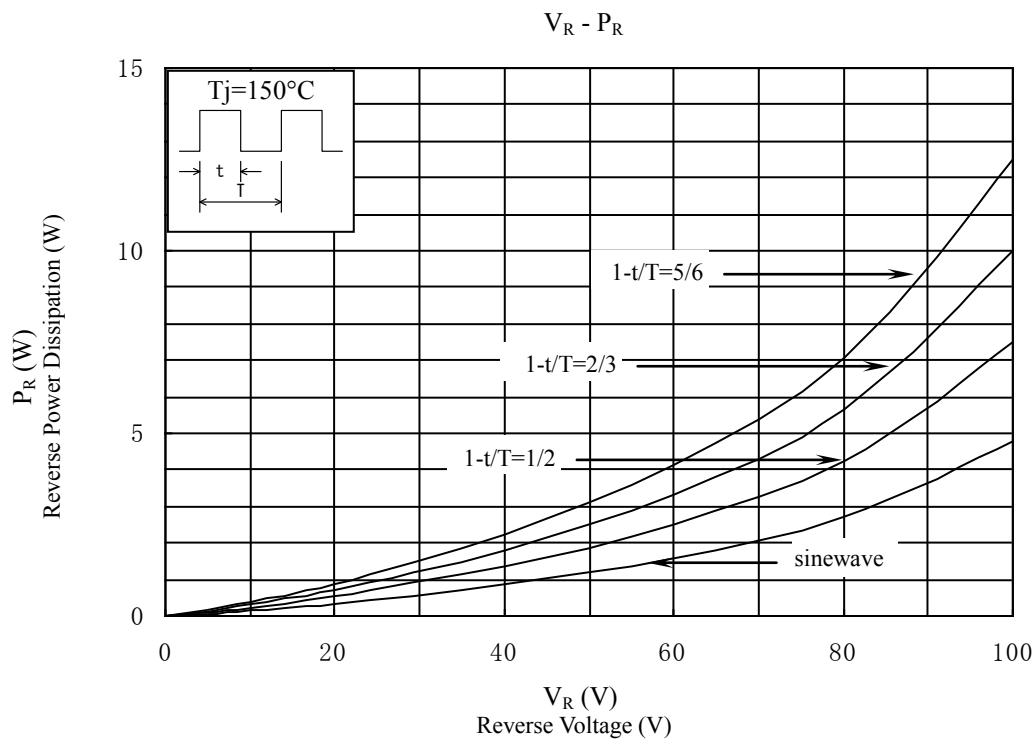
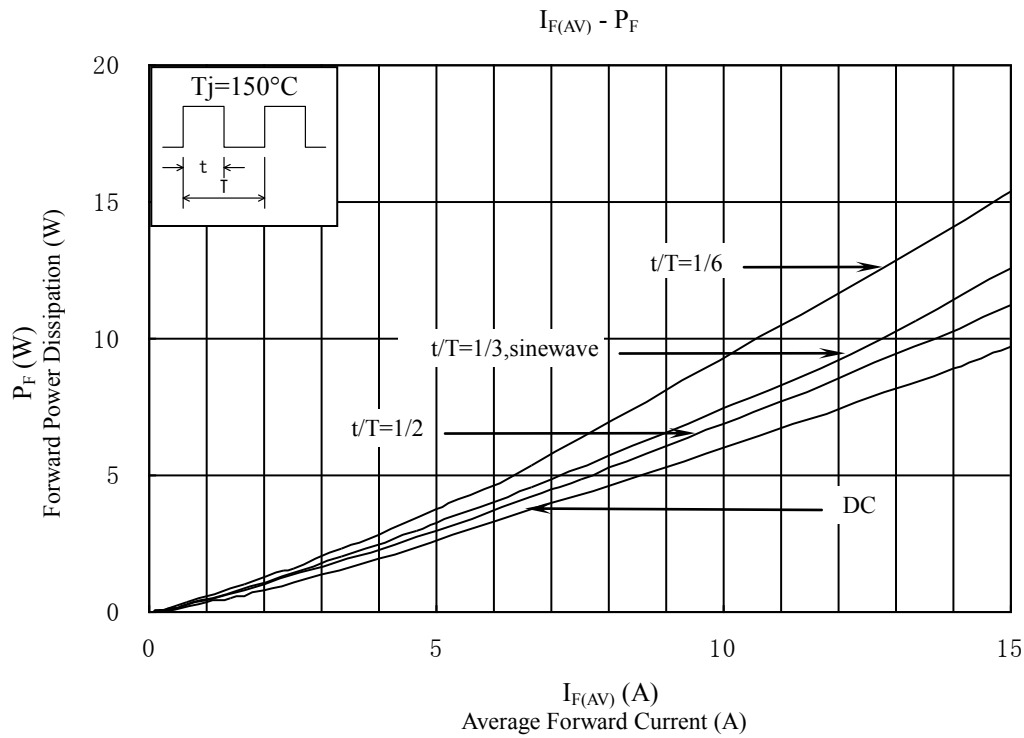
No.1,2,4&5 show ratings per one chip.

5. Electrical characteristics (Ta=25°C , unless otherwise specified)

No.	Item	Symbol	Unit	Value	Conditions
1	Forward Voltage Drop	V_F	V	0.85 max.	$I_F=7.5A$
2	Reverse Leakage Current	I_R	μA	150 max.	$V_R=V_{RM}$
3	Reverse Leakage Current Under High Temperature	$H \cdot I_R$	mA	75 max.	$V_R=V_{RM}, T_j=150^{\circ}C$
4	Thermal Resistance	$R_{th(j-c)}$	$^{\circ}C/W$	4.0 max.	Between Junction and case

No.1,2&3 show characteristics per one chip.

6. Characteristics



7. Derating

